

NPN SILICON LOW NOISE RF TRANSISTOR

DESCRIPTION:

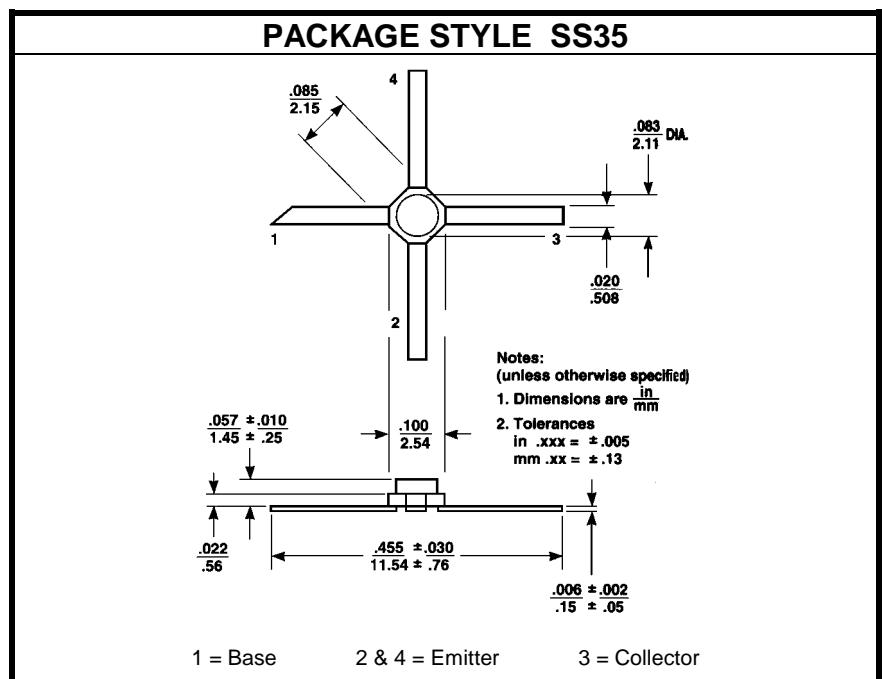
The **ALN64535** is a Common Emitter Device Designed for Low Noise Class A Amplifier Applications up to 4.0 GHz.

FEATURES INCLUDE:

- $N_F = 1.6$ dB Typical @ 2 GHz
- $|S_{21}|^2 = 11$ dB Typical @ 2 GHz
- Hermetic Ceramic Package

MAXIMUM RATINGS

I_C	60 mA
V_{CBO}	25 V
V_{CEO}	12 V
V_{EBO}	1.5 V
P_{DISS}	300 mW @ $T_A \leq 75^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	85°C/W


CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
I_{CBO}	$V_{CB} = 8$ V					100	nA
I_{EBO}	$V_{EB} = 1.0$ V					1.0	μA
h_{FE}	$V_{CE} = 8.0$ V	$I_C = 7.0$ mA		50		250	---
C_{CB}	$V_{CB} = 10$ V					0.6	pF
f_t	$V_{CE} = 10$ V	$I_C = 20$ mA	$f = 1.0$ GHz	8.0	8.5		GHz
$ S_{21} ^2$	$V_{CE} = 8$ V	$I_C = 20$ mA	$f = 2.0$ GHz	10	11		dB
NF GA	$V_{CE} = 8$ V	$I_C = 10$ mA	$f = 2.0$ GHz	10	11	2.5	dB